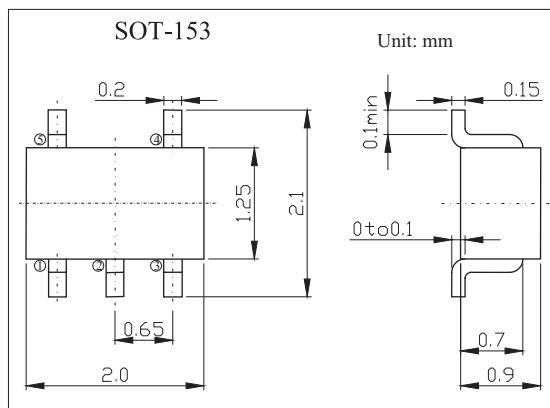
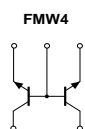


General purpose (Dual NPN Transistors)

FMW4

■ Features

- High breakdown voltage
- Power dissipation: $P_c=300\text{mW}$
- Collector Current: $I_c=50\text{mA}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current -Continuous	I_c	50	mA
Collector Power Dissipation(TOTAL)	P_c	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	$V_{(BR)CB0}$	$I_c = 50\mu\text{A}, I_E = 0$	120			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c = 1\text{mA}, I_B = 0$	120			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 50\mu\text{A}, I_c = 0$	5.0			V
Collector cutoff current	I_{cBO}	$V_{CB} = 100\text{V}, I_E = 0$			0.5	μA
Collector cutoff current	I_{EBO}	$V_{CE} = 4.0\text{V}, I_c = 0$			0.5	μA
DC current gain	h_{FE}	$V_{CE} = 60\text{V}, I_c = 2.0\text{mA}$	180		820	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 10\text{mA}, I_B = 1.0\text{mA}$			0.5	V
Transition frequency	f_T	$V_{CE} = 12\text{V}, I_c = 2\text{mA}, f = 100\text{MHz}$		140		MHz

■ Marking

Marking	W4